

NTTS2P02R2

Power MOSFET -2.4 Amps, -20 Volts

Single P-Channel Micro8™

Features

- Ultra Low $R_{DS(on)}$
- Higher Efficiency Extending Battery Life
- Logic Level Gate Drive
- Miniature Micro-8 Surface Mount Package
- Diode Exhibits High Speed, Soft Recovery
- Micro8 Mounting Information Provided
- Pb-Free Package is Available

Applications

- Power Management in Portable and Battery-Powered Products, i.e.: Cellular and Cordless Telephones, and PCMCIA Cards

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	-20	V
Gate-to-Source Voltage – Continuous	V_{GS}	± 8.0	V
Thermal Resistance – Junction-to-Ambient (Note 1)	$R_{\theta JA}$	160	$^\circ\text{C}/\text{W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	0.78	W
Continuous Drain Current @ $T_A = 25^\circ\text{C}$	I_D	-2.4	A
Continuous Drain Current @ $T_A = 70^\circ\text{C}$	I_D	-1.92	A
Pulsed Drain Current (Note 3)	I_{DM}	-20	A
Thermal Resistance – Junction-to-Ambient (Note 2)	$R_{\theta JA}$	88	$^\circ\text{C}/\text{W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	1.42	W
Continuous Drain Current @ $T_A = 25^\circ\text{C}$	I_D	-3.25	A
Continuous Drain Current @ $T_A = 70^\circ\text{C}$	I_D	-2.6	A
Pulsed Drain Current (Note 3)	I_{DM}	-30	A
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
Single Pulse Drain-to-Source Avalanche Energy – Starting $T_J = 25^\circ\text{C}$ ($V_{DD} = -20\text{ Vdc}$, $V_{GS} = -4.5\text{ Vdc}$, Peak $I_L = -5.0\text{ Apk}$, $L = 28\text{ mH}$, $R_G = 25\ \Omega$)	EAS	350	mJ
Maximum Lead Temperature for Soldering Purposes for 10 seconds	T_L	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Minimum FR-4 or G-10 PCB, Steady State.
2. Mounted onto a 2" square FR-4 Board (1 IN SQ, 2 oz Cu 0.06" thick single sided), Steady State.
3. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.



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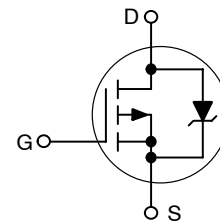
<http://onsemi.com>

-2.4 AMPERES

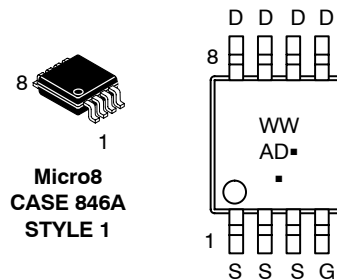
-20 VOLTS

$R_{DS(on)} = 90\text{ m}\Omega$

Single P-Channel



MARKING DIAGRAM & PIN ASSIGNMENT



AD = Specific Device Code
WW = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTTS2P02R2	Micro8	4000/Tape & Reel
NTTS2P02R2G	Micro8 (Pb-Free)	4000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTTS2P02R2

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted) (Note 4)

Characteristic	Symbol	Min	Typ	Max	Unit	
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = -250 μAdc) Temperature Coefficient (Positive)	V _{(BR)DSS}	-20 -	- -12.7	- -	Vdc mV/°C	
Zero Gate Voltage Drain Current (V _{GS} = 0 Vdc, V _{DS} = -16 Vdc, T _J = 25°C) (V _{GS} = 0 Vdc, V _{DS} = -16 Vdc, T _J = 125°C)	I _{DSS}	- -	- -	-1.0 -25	μAdc	
Zero Gate Voltage Drain Current (V _{GS} = 0 Vdc, V _{DS} = -20 Vdc, T _J = 25°C)	I _{DSS}	-	-	-5.0	μAdc	
Gate-Body Leakage Current (V _{GS} = -8 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	-	-	-100	nAdc	
Gate-Body Leakage Current (V _{GS} = +8 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	-	-	100	nAdc	
ON CHARACTERISTICS						
Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = -250 μAdc) Temperature Coefficient (Negative)	V _{GS(th)}	-0.5 -	-0.90 2.5	-1.4 -	Vdc mV/°C	
Static Drain-to-Source On-State Resistance (V _{GS} = -4.5 Vdc, I _D = -2.4 Adc) (V _{GS} = -2.7 Vdc, I _D = -1.2 Adc) (V _{GS} = -2.5 Vdc, I _D = -1.2 Adc)	R _{DS(on)}	- - -	0.070 0.100 0.110	0.090 0.130 -	Ω	
Forward Transconductance (V _{DS} = -10 Vdc, I _D = -1.2 Adc)	g _{FS}	2.0	4.2	-	Mhos	
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V _{DS} = -16 Vdc, V _{GS} = 0 Vdc, f = 1.0 MHz)	C _{iss}	-	550	-	pF
Output Capacitance		C _{oss}	-	200	-	
Reverse Transfer Capacitance		C _{rss}	-	100	-	
SWITCHING CHARACTERISTICS (Notes 5 & 6)						
Turn-On Delay Time	(V _{DD} = -10 Vdc, I _D = -2.4 Adc, V _{GS} = -4.5 Vdc, R _G = 6.0 Ω)	t _{d(on)}	-	10	-	ns
Rise Time		t _r	-	31	-	
Turn-Off Delay Time		t _{d(off)}	-	33	-	
Fall Time		t _f	-	29	-	
Turn-On Delay Time	(V _{DD} = -10 Vdc, I _D = -1.2 Adc, V _{GS} = -2.7 Vdc, R _G = 6.0 Ω)	t _{d(on)}	-	15	-	ns
Rise Time		t _r	-	40	-	
Turn-Off Delay Time		t _{d(off)}	-	35	-	
Fall Time		t _f	-	35	-	
Total Gate Charge	(V _{DS} = -16 Vdc, V _{GS} = -4.5 Vdc, I _D = -2.4 Adc)	Q _{tot}	-	10	18	nC
Gate-Source Charge		Q _{gs}	-	1.5	-	
Gate-Drain Charge		Q _{gd}	-	5.0	-	
BODY-DRAIN DIODE RATINGS (Note 5)						
Diode Forward On-Voltage (I _S = -2.4 Adc, V _{GS} = 0 Vdc) (I _S = -2.4 Adc, V _{GS} = 0 Vdc, T _J = 125°C)	V _{SD}	- -	-0.88 -0.75	-1.0 -	Vdc	
Reverse Recovery Time (I _S = -2.4 Adc, V _{GS} = 0 Vdc, dI _S /dt = 100 A/μs)	t _{rr}	-	37	-	ns	
	t _a	-	16	-		
	t _b	-	21	-		
Reverse Recovery Stored Charge	Q _{RR}	-	0.025	-	μC	

4. Handling precautions to protect against electrostatic discharge are mandatory.

5. Indicates Pulse Test: Pulse Width = 300 μs max, Duty Cycle = 2%.

6. Switching characteristics are independent of operating junction temperature.

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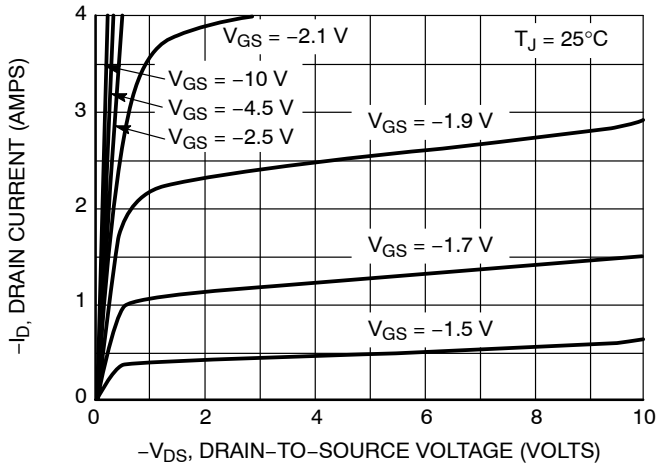


Figure 1. On-Region Characteristics.

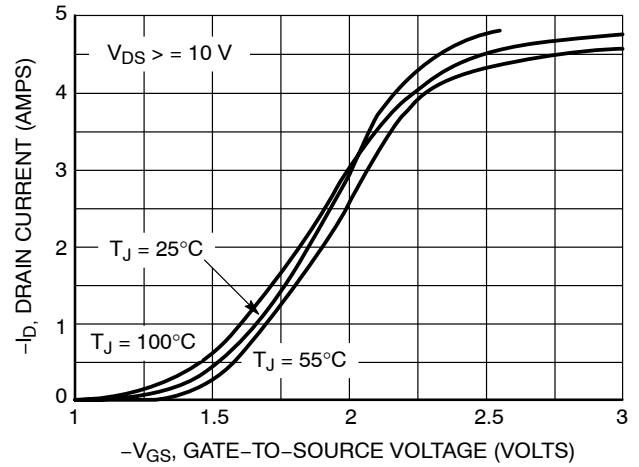


Figure 2. Transfer Characteristics.

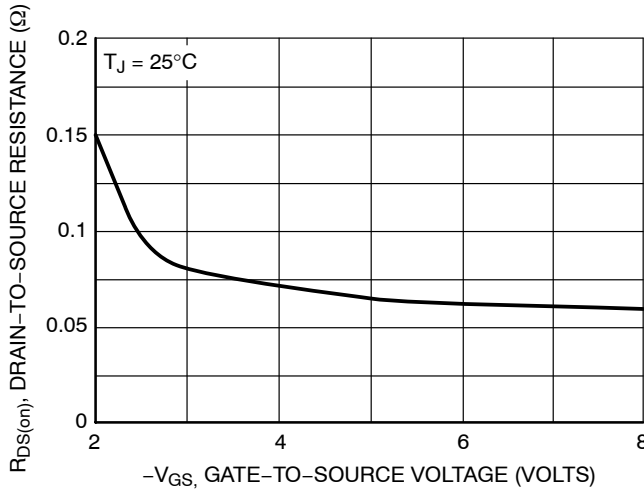


Figure 3. On-Resistance vs. Gate-to-Source Voltage.

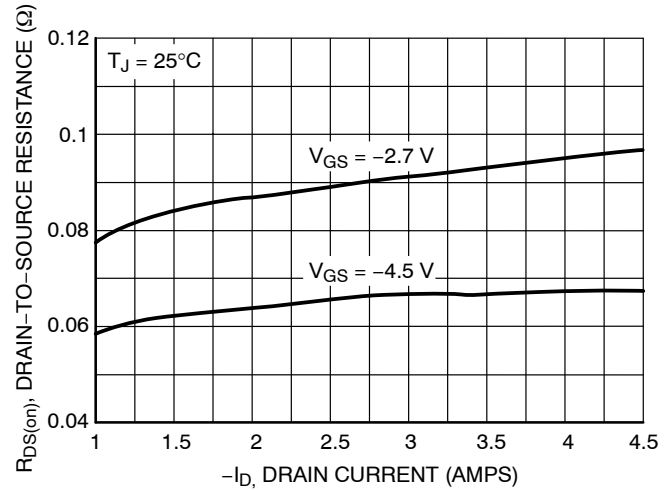


Figure 4. On-Resistance vs. Drain Current and Gate Voltage.

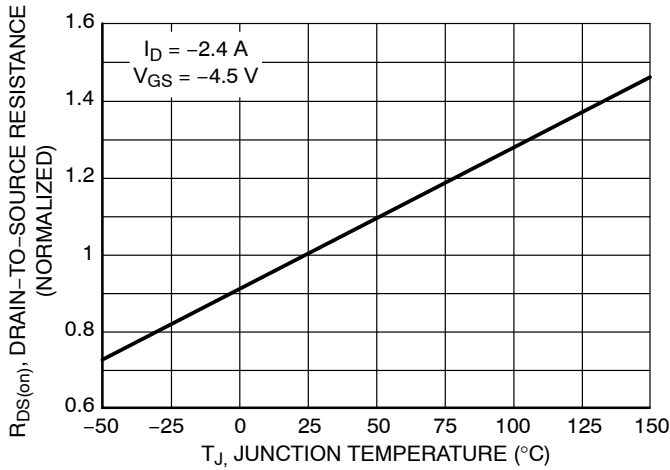


Figure 5. On-Resistance Variation with Temperature.

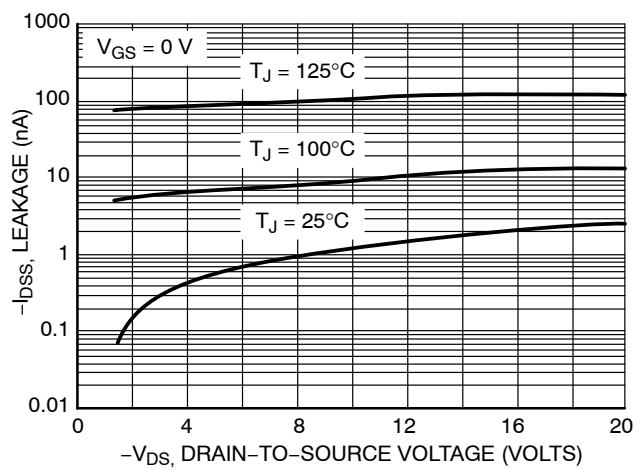


Figure 6. Drain-to-Source Leakage Current vs. Voltage.

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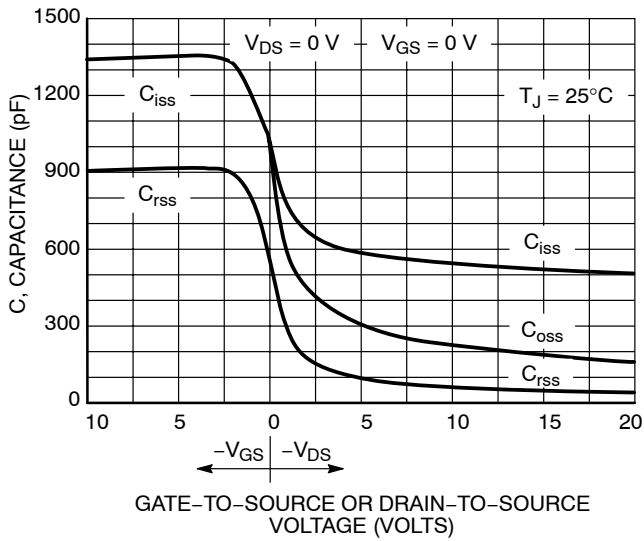


Figure 7. Capacitance Variation

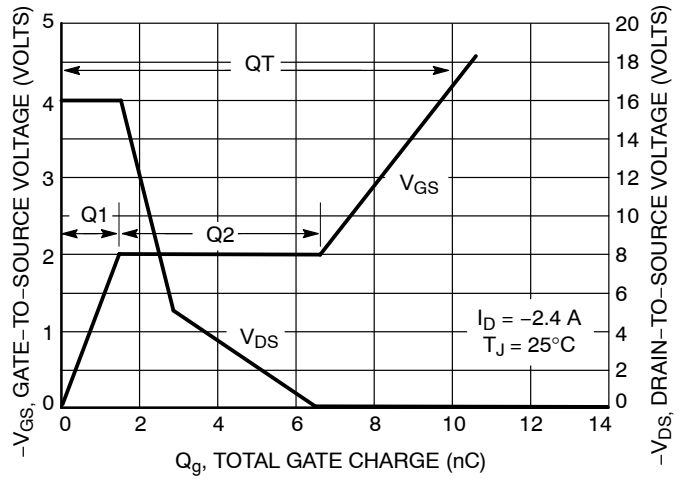


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

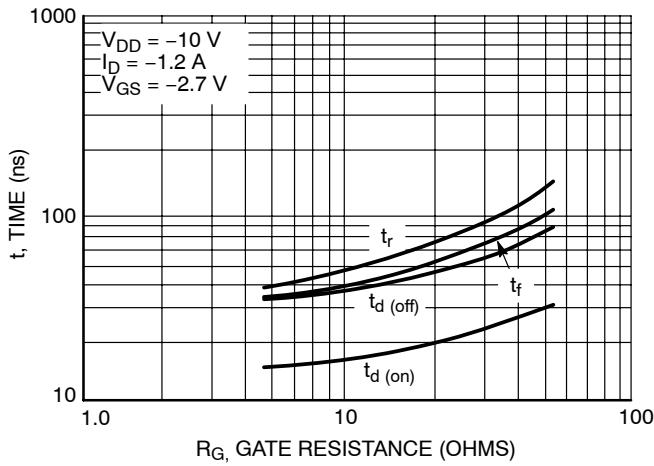


Figure 9. Resistive Switching Time Variation versus Gate Resistance

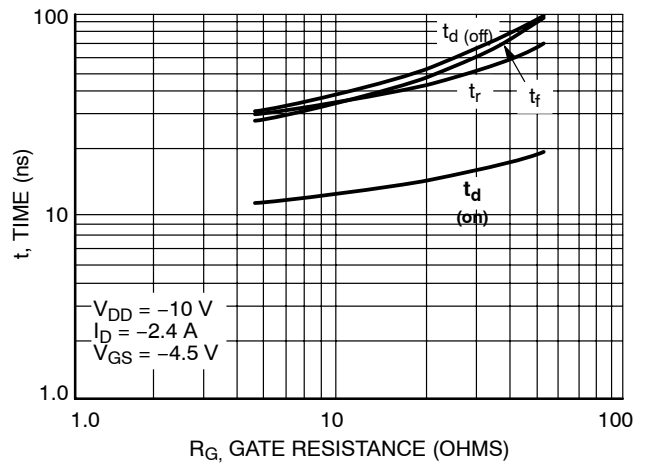


Figure 10. Resistive Switching Time Variation versus Gate Resistance

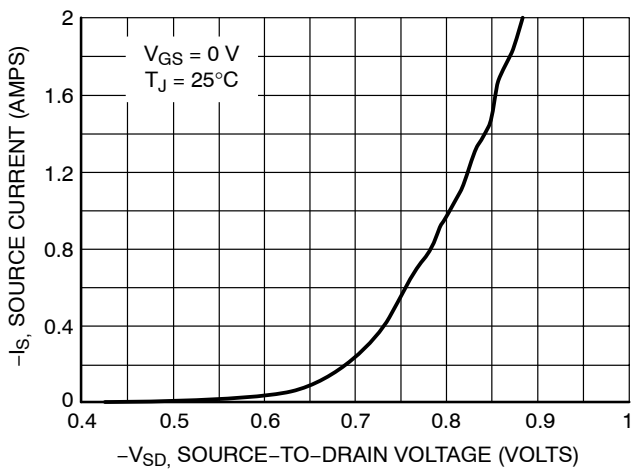


Figure 11. Diode Forward Voltage versus Current

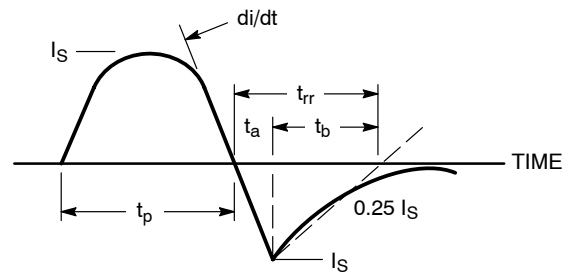


Figure 12. Diode Reverse Recovery Waveform

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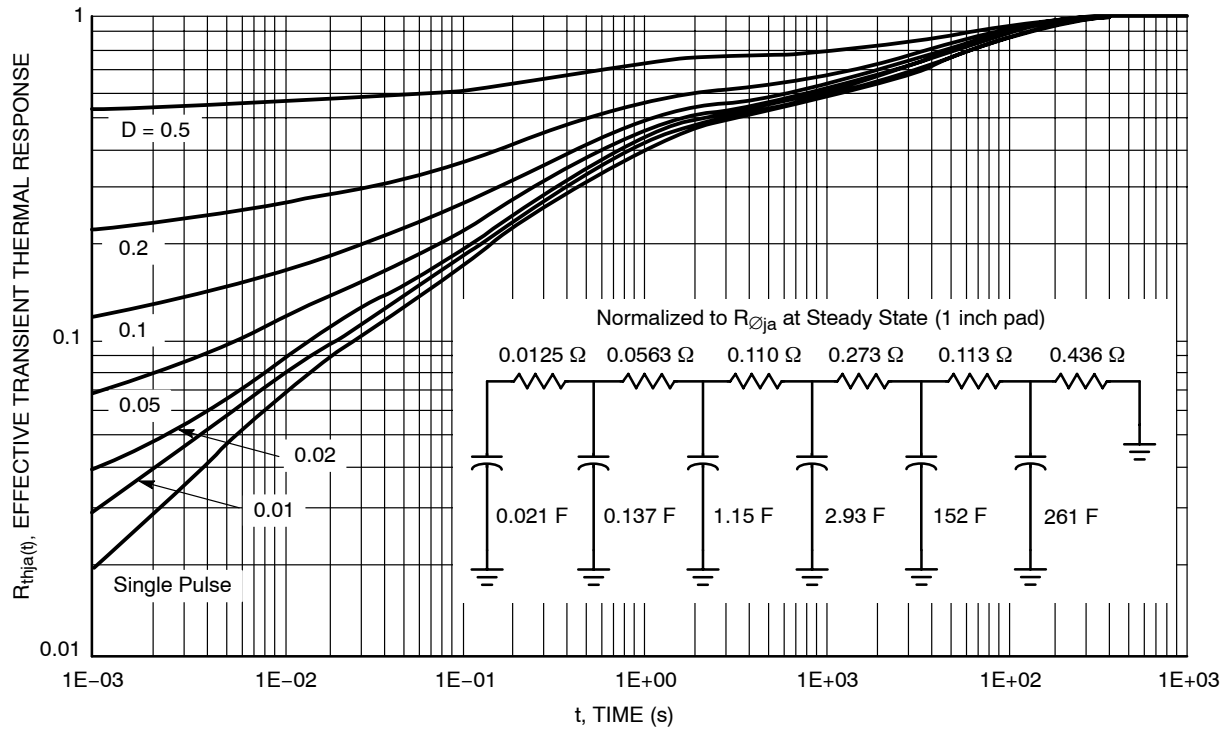


Figure 13. FET Thermal Response.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

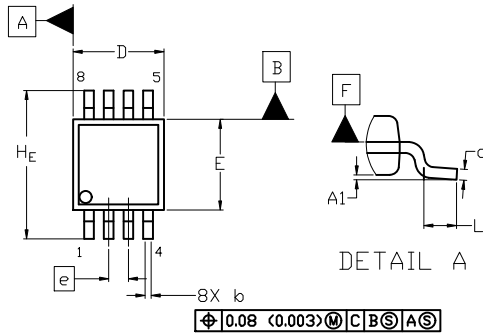
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SCALE 2:1

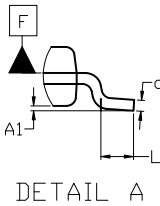
Micro8 CASE 846A-02 ISSUE K

DATE 16 JUL 2020



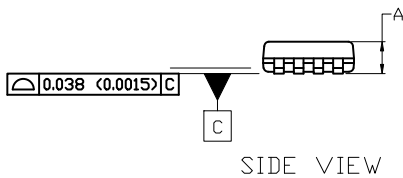
TOP VIEW

NOTE 3

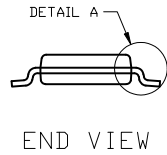


DETAIL A

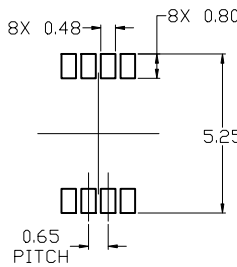
$\phi 0.08$ (0.003) M C B S A S



SIDE VIEW



END VIEW

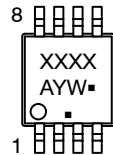


RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.05	0.08	0.15
b	0.25	0.33	0.40
c	0.13	0.18	0.23
D	2.90	3.00	3.10
E	2.90	3.00	3.10
e	0.65 BSC		
H _E	4.75	4.90	5.05
L	0.40	0.55	0.70

GENERIC MARKING DIAGRAM*



- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:

- PIN 1. SOURCE
- 2. SOURCE
- 3. SOURCE
- 4. GATE
- 5. DRAIN
- 6. DRAIN
- 7. DRAIN
- 8. DRAIN

STYLE 2:

- PIN 1. SOURCE 1
- 2. GATE 1
- 3. SOURCE 2
- 4. GATE 2
- 5. DRAIN 2
- 6. DRAIN 2
- 7. DRAIN 1
- 8. DRAIN 1

STYLE 3:

- PIN 1. N-SOURCE
- 2. N-GATE
- 3. P-SOURCE
- 4. P-GATE
- 5. P-DRAIN
- 6. P-DRAIN
- 7. N-DRAIN
- 8. N-DRAIN

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